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12-Stage Binary Ripple Counter

High-Performance Silicon-Gate CMOS

The MC74C4040A is identical in pinout to the standard CMOS MC14040. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of 12 master-slave flip-flops. The output of each flip-flop feeds the next and the frequency at each output is half of that of the preceding one. The state counter advances on the negative-going edge of the Clock input. Reset is asynchronous and active-high.

State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and may have to be gated with the Clock of the HC4040A for some designs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With JEDEC Standard No. 7A Requirements
- Chip Complexity: 398 FETs or 99.5 Equivalent Gates
- Pb-Free Packages are Available*



ON Semiconductor®

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MARKING DIAGRAMS



PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- Q1 Q2 - Q3 5 Q4 3 Q5 Clock 10 2 Q6 4 Q7 13 Q8 12 Q9 14 Q10 15 Q11 1 Q12 Pin 16 = V_{CC} Pin 8 = GND 11 Reset -

Figure 1. Logic Diagram

FUNCTION TABLE

Clock	Reset	Output State
	L	No Charge
	L	Advance to Next State
X	Н	All Outputs Are Low
		·

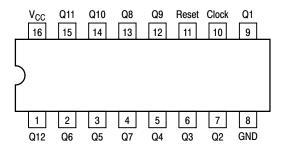


Figure 2. Pinout: 16-Lead Plastic Package (Top View)

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC4040AN	PDIP-16	2000 Units / Box
MC74HC4040ANG	PDIP-16 (Pb-Free)	2000 Units / Box
MC74HC4040AD	SOIC-16	48 Units / Rail
MC74HC4040ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC4040ADR2	SOIC-16	2500 Units / Reel
MC74HC4040ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC4040ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC4040ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC4040AF	SOEIAJ-16	50 Units / Rail
MC74HC4040AFG	SOEIAJ-16 (Pb-Free)	50 Units / Rail
MC74HC4040AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC4040AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or $V_{\rm CC}$). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature Range, All Package Types	– 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0 0	1000 600 500 400	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	Guara	nteed Lin	nit	
Symbol	Parameter	Condition	v	-55 to 25°C	≤85°C	≤125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 V \text{ or } V_{CC} - 0.1 V$ $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 V \text{ or } V_{CC} - 0.1 V$ $ I_{out} \le 20 \mu A$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{aligned} V_{in} = & V_{IH} \text{ or } V_{IL} & I_{out} \leq 2 \\ & I_{out} \leq 4 \\ & I_{out} \leq 5 \end{aligned}$.0mA 4.5	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V

DC CHARACTERISTICS (Voltages Referenced to GND)

				v _{cc}	Guaranteed Limit			
Symbol	Parameter	Conditi	ion	v	–55 to 25°C	≤85°C	≤125°C	Unit
		$V_{in} = V_{IH}$ or V_{IL}	$\begin{aligned} I_{out} &\leq 2.4 \text{mA} \\ I_{out} &\leq 4.0 \text{mA} \\ I_{out} &\leq 5.2 \text{mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND		6.0	±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$		6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

		V _{CC}	Guara			
Symbol	Parameter	V	–55 to 25°C	≤85°C	≤125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 4)	2.0 3.0 4.5 6.0	10 15 30 50	9.0 14 28 45	8.0 12 25 40	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q1* (Figures 1 and 4)	2.0 3.0 4.5 6.0	96 63 31 25	106 71 36 30	115 88 40 35	ns
t _{PHL}	Maximum Propagation Delay, Reset to Any Q (Figures 2 and 4)	2.0 3.0 4.5 6.0	45 30 30 26	52 36 35 32	65 40 40 35	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Qn to Qn+1 (Figures 3 and 4)	2.0 3.0 4.5 6.0	69 40 17 14	80 45 21 15	90 50 28 22	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 4)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 15	110 36 22 19	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

* For $T_A = 25^{\circ}C$ and $C_L = 50$ pF, typical propagation delay from Clock to other Q outputs may be calculated with the following equations: $V_{CC} = 2.0 \text{ V}$: $t_P = [93.7 + 59.3 \text{ (n-1)}] \text{ ns}$ $V_{CC} = 4.5 \text{ V}$: $t_P = [30.25 + 14.6 \text{ (n-1)}] \text{ ns}$ $V_{CC} = 6.0 \text{ V}$: $t_P = [24.4 + 12 \text{ (n-1)}] \text{ ns}$

Ī			Typical @ 25°C, V _{CC} = 5.0 V	
	C_{PD}	Power Dissipation Capacitance (Per Package)*	31	pF

^{*} Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

		V _{CC}	Guara			
Symbol	Parameter	v	-55 to 25°C	≤ 85 °C	≤125°C	Unit
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0 3.0 4.5 6.0	30 20 5 4	40 25 8 6	50 30 12 9	ns
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	70 40 15 13	80 45 19 16	90 50 24 20	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

PIN DESCRIPTIONS

INPUTS

Clock (Pin 10)

Negative-edge triggering clock input. A high-to-low transition on this input advances the state of the counter.

Reset (Pin 11)

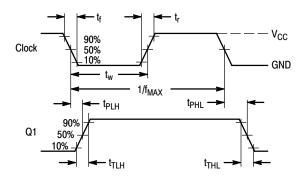
Active-high reset. A high level applied to this input asynchronously resets the counter to its zero state, thus forcing all Q outputs low.

OUTPUTS

Q1 thru Q12 (Pins 9, 7, 6, 5, 3, 2, 4, 13, 12, 14, 15, 1)

Active-high outputs. Each Qn output divides the Clock input frequency by 2^N .

SWITCHING WAVEFORMS





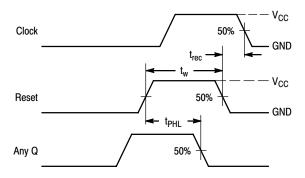
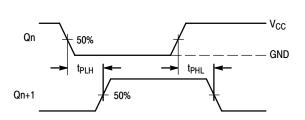
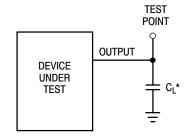


Figure 4.

SWITCHING WAVEFORMS (continued)





*Includes all probe and jig capacitance

Figure 5.

Figure 6. Test Circuit

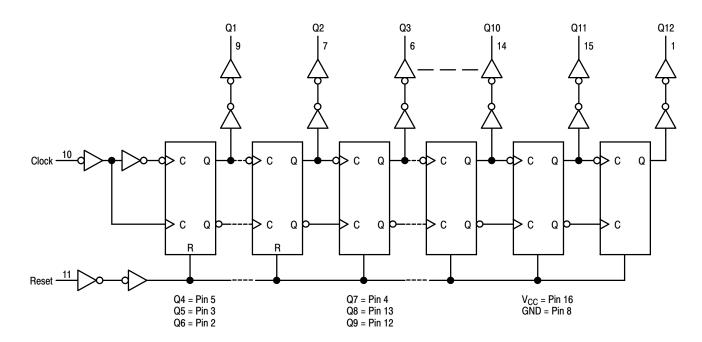


Figure 7. Expanded Logic Diagram

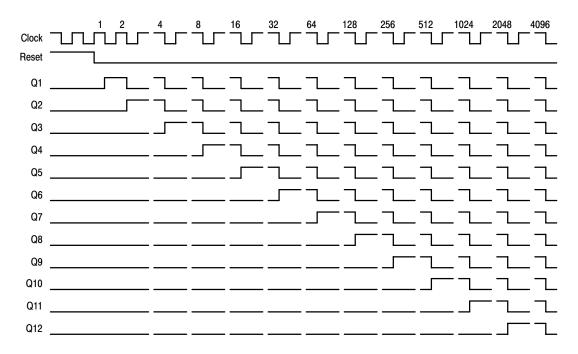


Figure 8. Timing Diagram

APPLICATIONS INFORMATION

Time-Base Generator

A 60Hz sinewave obtained through a 100 K resistor connected to a 120 Vac power line through a step down transformer is applied to the input of the MC54/74HC14A, Schmitt-trigger inverter. The HC14A squares—up the input

waveform and feeds the HC4040A. Selecting outputs Q5, Q10, Q11, and Q12 causes a reset every 3600 clocks. The HC20 decodes the counter outputs, produces a single (narrow) output pulse, and resets the binary counter. The resulting output frequency is 1.0 pulse/minute.

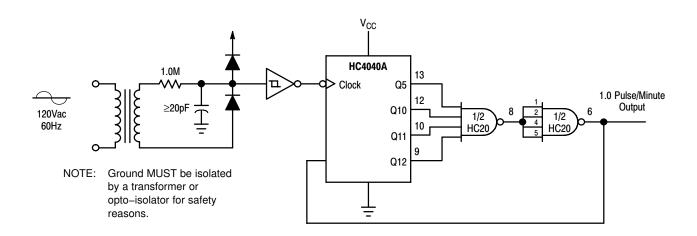
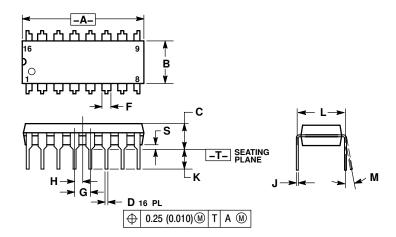


Figure 9. Time-Base Generator

PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

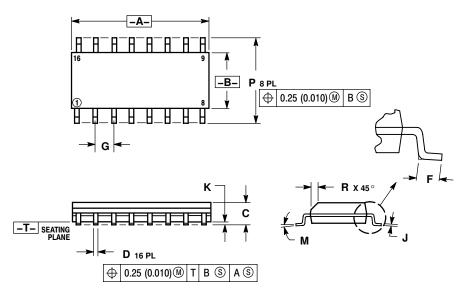
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
М	0°	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

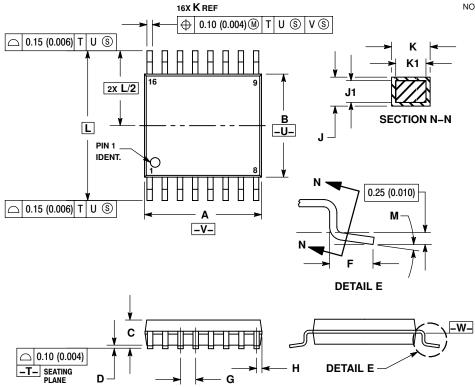
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIGN.

- MAXIMUM MOLD PHOLICISION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	1.27 BSC		BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A**



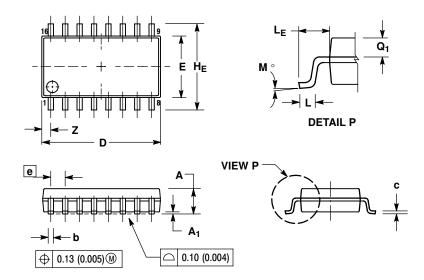
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

 - (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL
 - DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
O		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0°	8°	0°	8 °	

PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O**



NOTES:

- 1. DIMENSIC Y14.5M, 1982 DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER
- B. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (U.U.D) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
Ь	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031

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